

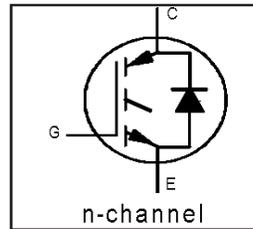
IRG4PSH71KDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

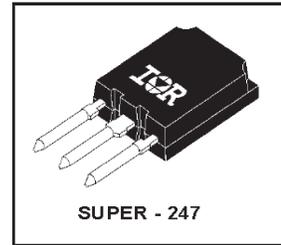
- Hole-less clip/pressure mount package compatible with TO-247 and TO-264, with reinforced pins
- High short circuit rating IGBTs, optimized for motorcontrol
- Minimum switching losses combined with low conduction losses
- Tightest parameter distribution
- IGBT co-packaged with ultrafast soft recovery antiparallel diode
- Creepage distance increased to 5.35mm
- Lead-Free



$V_{CES} = 1200V$
$V_{CE(on) typ.} = 2.97V$
@ $V_{GE} = 15V, I_C = 42A$

Benefits

- Highest current rating copack IGBT
- Maximum power density, twice the power handling of the TO-247, less space than TO-264
- HEXFRED™ diode optimized for operation with IGBT, to minimize EMI, noise and switching losses



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	78	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	42	
I_{CM}	Pulsed Collector Current ①	156	
I_{LM}	Clamped Inductive Load Current ②	156	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	42	
I_{FM}	Diode Maximum Forward Current	156	
t_{sc}	Short Circuit Withstand Time	10	μs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	350	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	140	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance\ Mechanical

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	---	---	0.36	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	---	---	0.69	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	---	0.24	---	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	---	38	
	Recommended Clip Force	20.0(2.0)	---	---	N (kgf)
	Weight	---	6 (0.21)	---	g (oz)

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage ^③	1200	—	—	V	V _{GE} = 0V, I _C = 250μA
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	1.1	—	V/°C	V _{GE} = 0V, I _C = 10mA
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	—	2.97	3.9	V	I _C = 42A, V _{GE} = 15V See Fig. 2, 5
		—	3.44	—		
		—	2.60	—		
V _{GE(th)}	Gate Threshold Voltage	3.0	—	6.0		V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)} /ΔT _J	Temperature Coeff. of Threshold Voltage	—	-12	—	mV/°C	V _{CE} = V _{GE} , I _C = 1.5mA
g _{fe}	Forward Transconductance ^④	25	38	—	S	V _{CE} = 50V, I _C = 42A
I _{CES}	Zero Gate Voltage Collector Current	—	—	500	μA	V _{GE} = 0V, V _{CE} = 1200V
		—	—	10	mA	V _{GE} = 0V, V _{CE} = 1200V, T _J = 150°C
V _{FM}	Diode Forward Voltage Drop	—	2.5	3.7	V	I _C = 42A, See Fig. 13
		—	2.4	—		
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	410	610	nC	I _C = 42A V _{CC} = 400V, See Fig.8 V _{GE} = 15V
Q _{ge}	Gate - Emitter Charge (turn-on)	—	47	70		
Q _{gc}	Gate - Collector Charge (turn-on)	—	145	220		
t _{d(on)}	Turn-On Delay Time	—	67	—	ns	T _J = 25°C I _C = 42A, V _{CC} = 800V V _{GE} = 15V, R _G = 5.0Ω
t _r	Rise Time	—	84	—		
t _{d(off)}	Turn-Off Delay Time	—	230	350		
t _f	Fall Time	—	130	190		
E _{on}	Turn-On Switching Loss	—	5.68	—	mJ	Energy losses include "tail" and diode reverse recovery See Fig. 9,10,18
E _{off}	Turn-Off Switching Loss	—	3.23	—		
E _{ts}	Total Switching Loss	—	8.90	11.6		
t _{sc}	Short Circuit Withstand Time	10	—	—	μs	V _{CC} = 720V, T _J = 125°C V _{GE} = 15V, R _G = 5.0Ω
t _{d(on)}	Turn-On Delay Time	—	65	—	ns	T _J = 150°C, See Fig. 11,18 I _C = 42A, V _{CC} = 800V V _{GE} = 15V, R _G = 5.0Ω
t _r	Rise Time	—	87	—		
t _{d(off)}	Turn-Off Delay Time	—	370	—		
t _f	Fall Time	—	290	—		
E _{ts}	Total Switching Loss	—	13.7	—	mJ	Energy losses include "tail" and diode reverse recovery
L _E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C _{ies}	Input Capacitance	—	5770	—	pF	V _{GE} = 0V V _{CC} = 30V, See Fig. 7 f = 1.0MHz
C _{oes}	Output Capacitance	—	400	—		
C _{res}	Reverse Transfer Capacitance	—	100	—		
t _{rr}	Diode Reverse Recovery Time	—	107	160	ns	T _J = 25°C, See Fig. 14 T _J = 125°C
		—	160	240		
I _{rr}	Diode Peak Reverse Recovery Current	—	10	15	A	T _J = 25°C, See Fig. 15 T _J = 125°C
		—	16	24		
Q _{rr}	Diode Reverse Recovery Charge	—	680	1020	nC	T _J = 25°C, See Fig. 16 T _J = 125°C
		—	1400	2100		
di _(rec) /dt	Diode Peak Rate of Fall of Recovery During t _b	—	250	—	A/μs	T _J = 25°C, See Fig. 17 T _J = 125°C
		—	320	—		

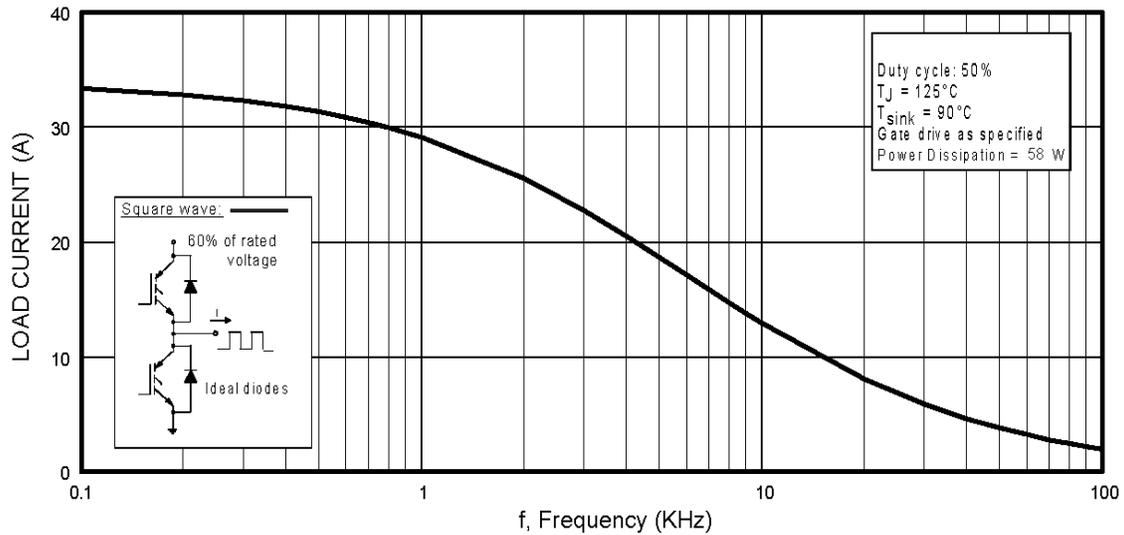


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

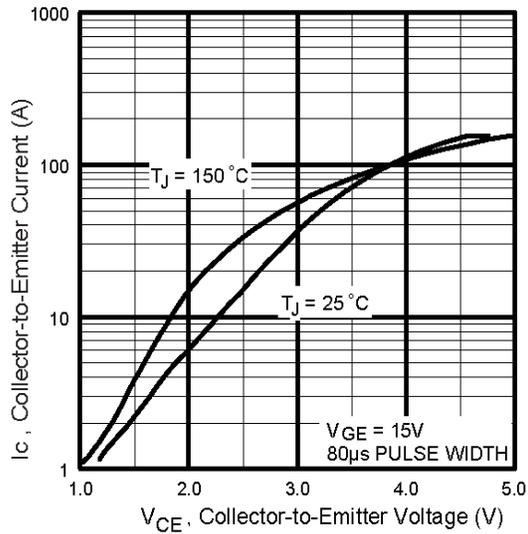


Fig. 2 - Typical Output Characteristics

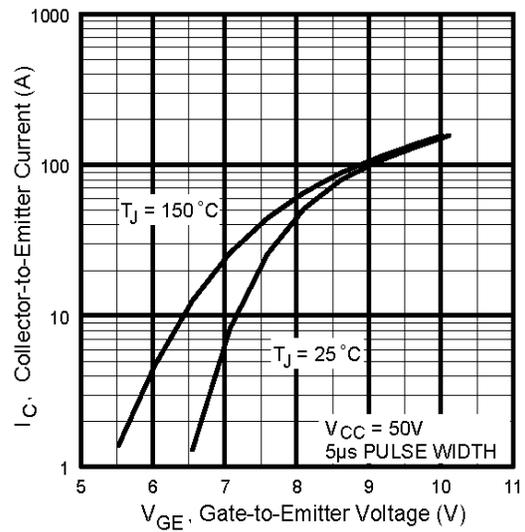


Fig. 3 - Typical Transfer Characteristics

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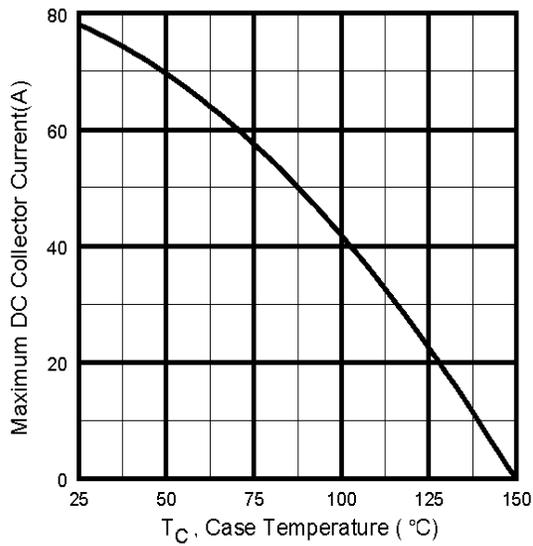


Fig. 4 - Maximum Collector Current vs. Case Temperature

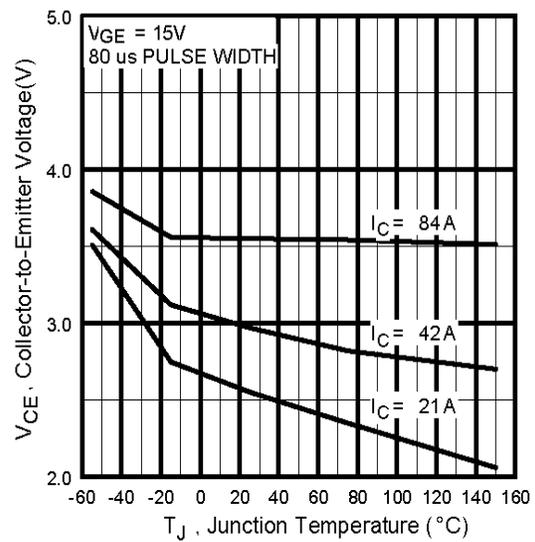


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

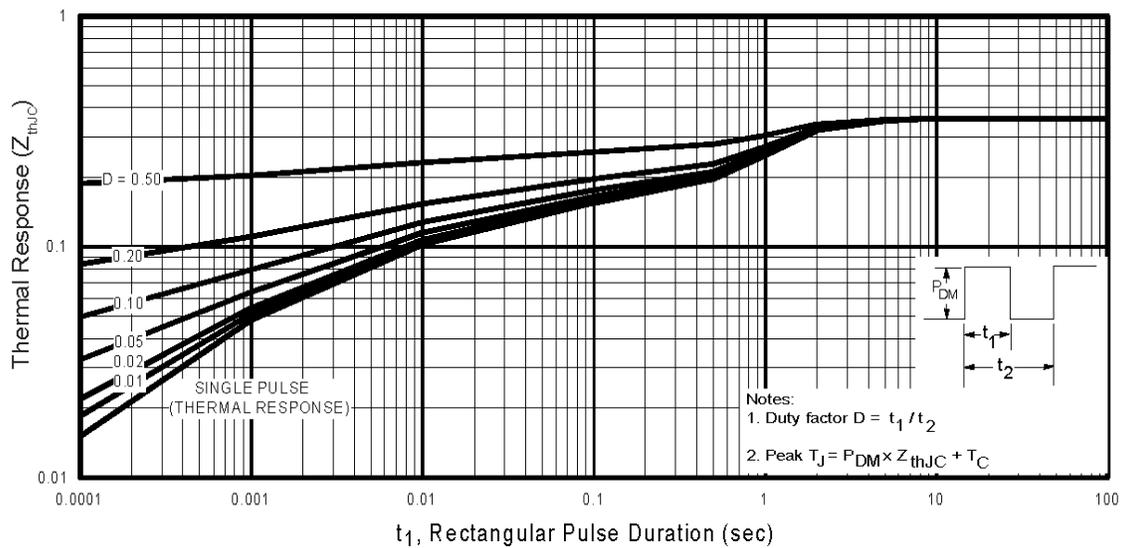


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

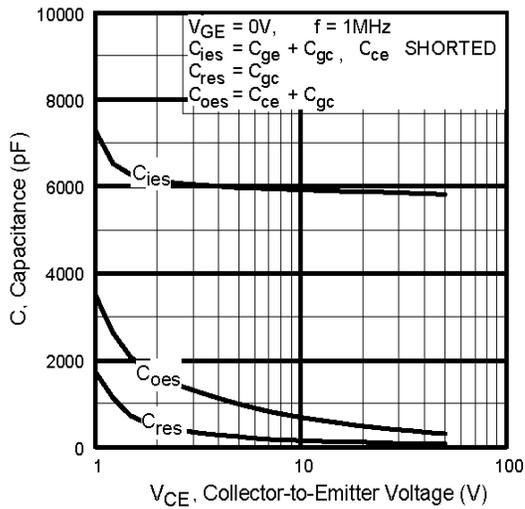


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

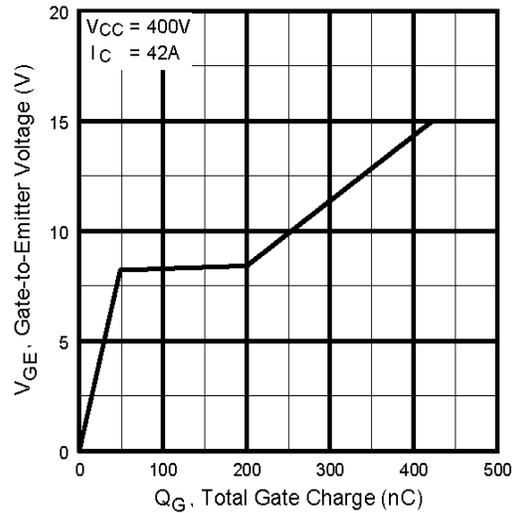


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

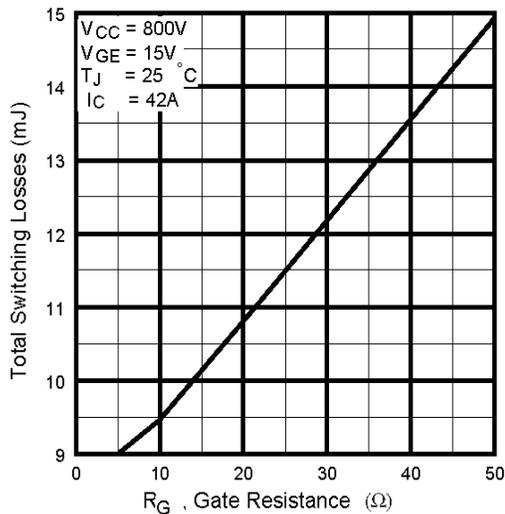


Fig. 9 - Typical Switching Losses vs. Gate Resistance

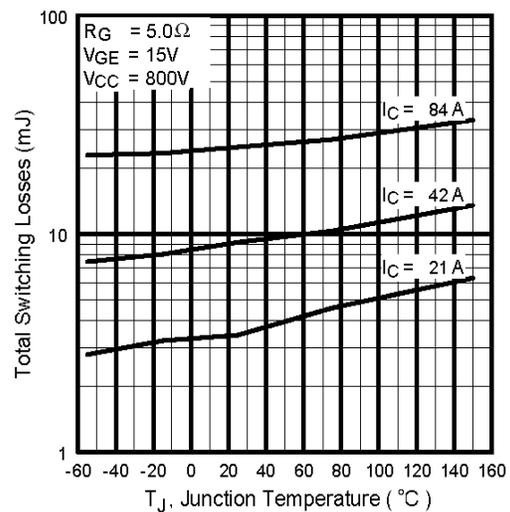
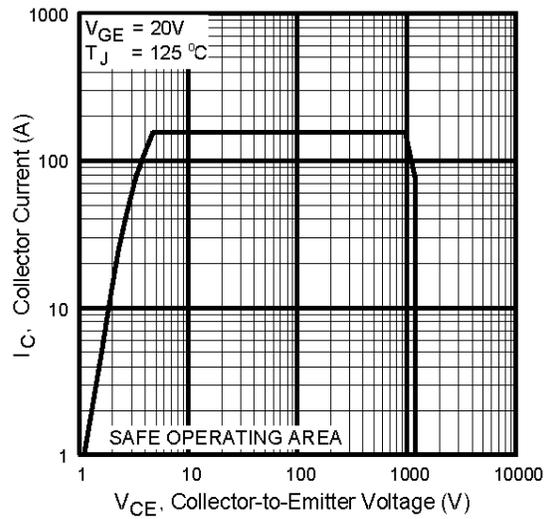
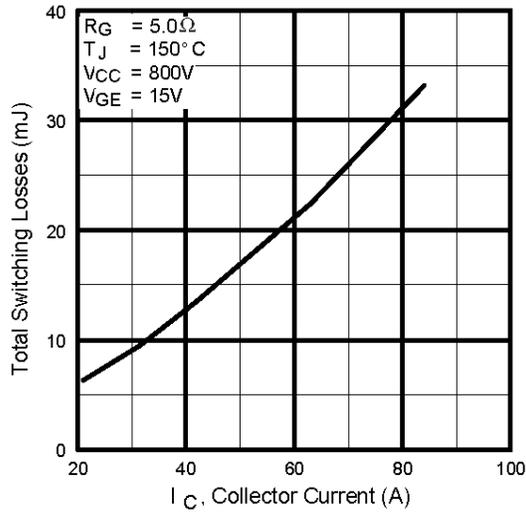


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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Collector-to-Emitter Current

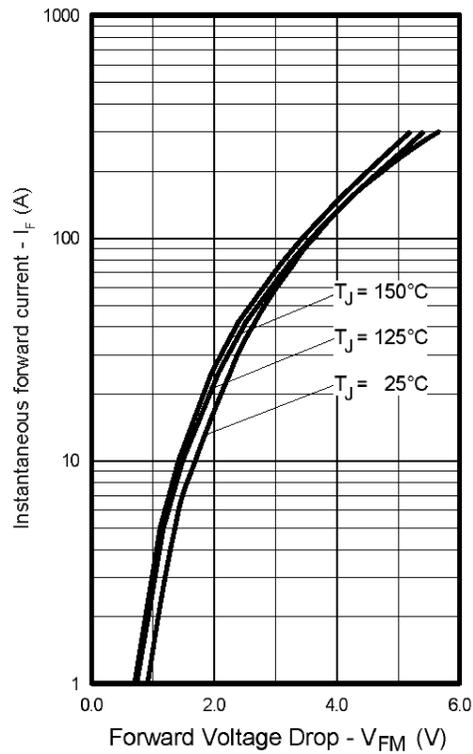


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

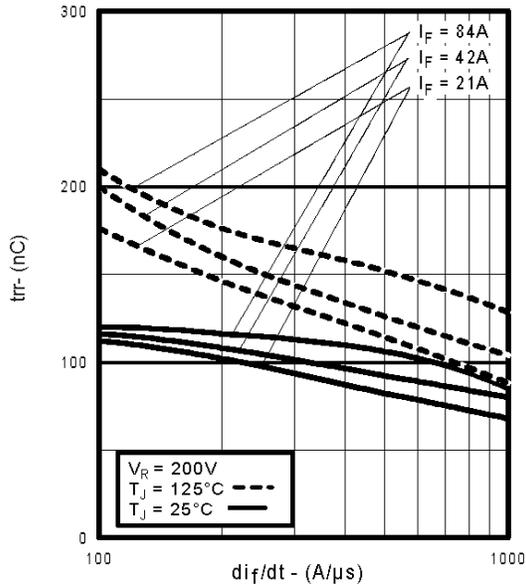


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

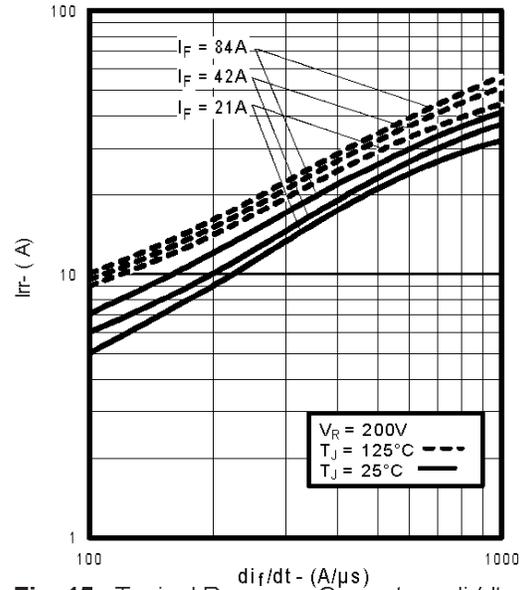


Fig. 15 - Typical Recovery Current vs. di_f/dt

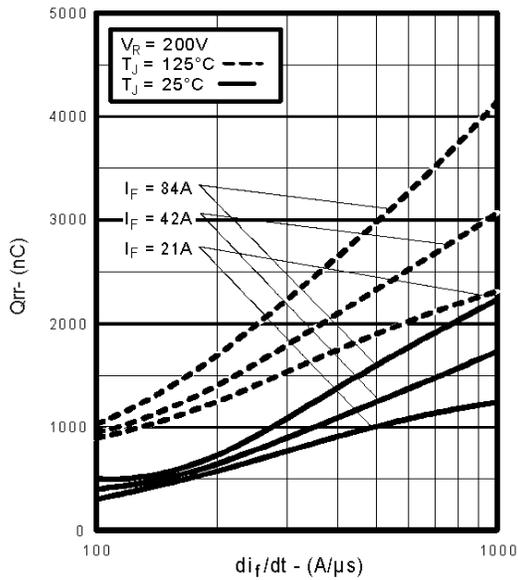


Fig. 16 - Typical Stored Charge vs. di_f/dt

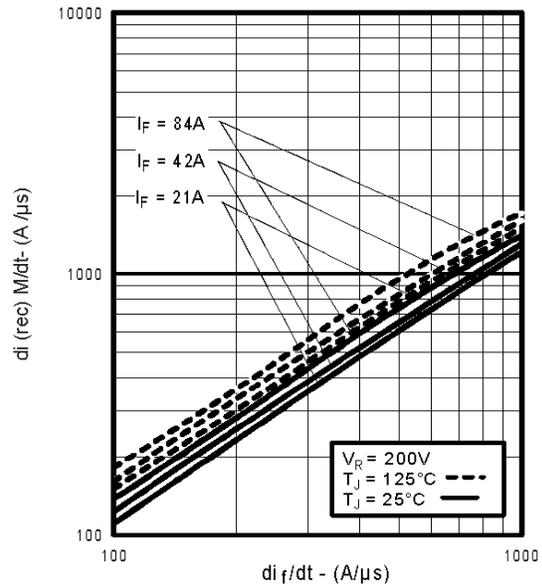


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

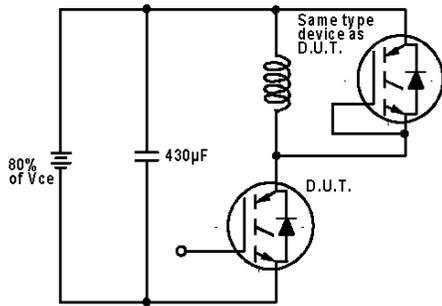


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

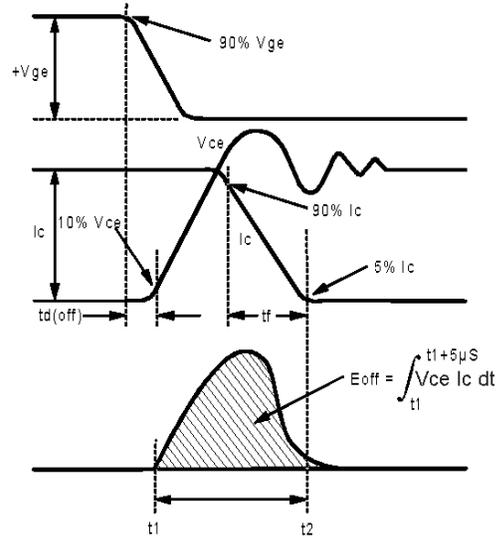


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

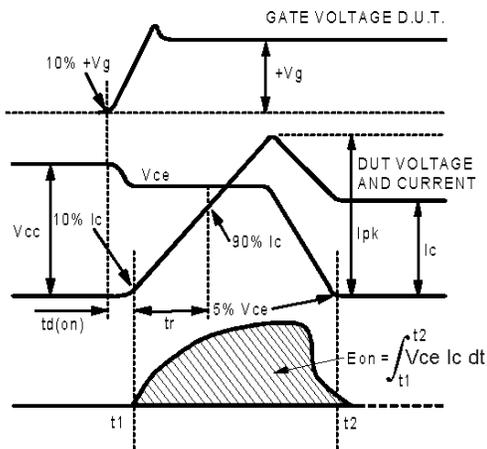


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

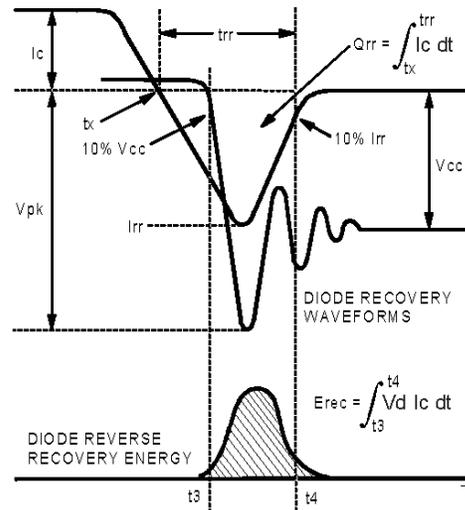


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

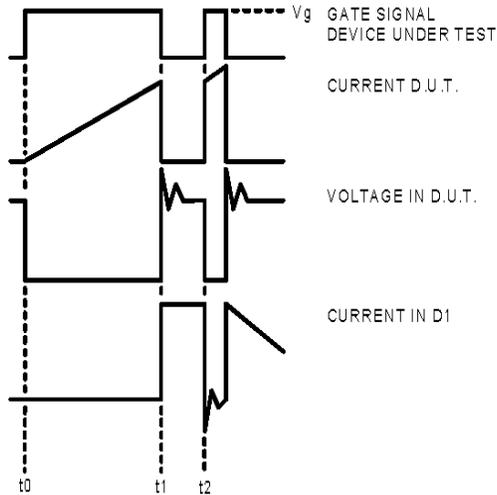


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

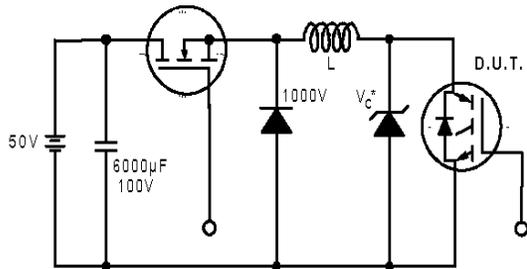


Figure 19. Clamped Inductive Load Test Circuit

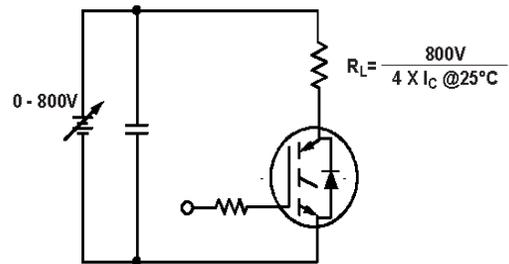
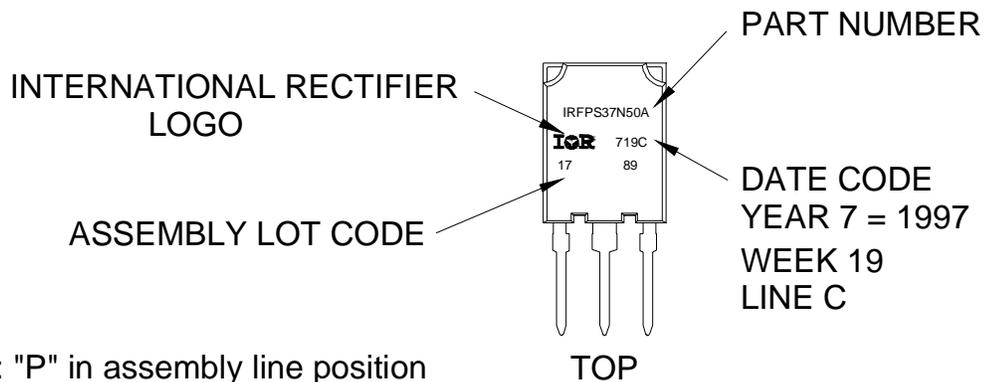


Figure 20. Pulsed Collector Current Test Circuit

Super-247 (TO-274AA) Part Marking Information

EXAMPLE: THIS IS AN IRFPS37N50A WITH
ASSEMBLY LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



Note: "P" in assembly line position indicates "Lead-Free"

Data and specifications subject to change without notice.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

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